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His research interests are mainly focused in the field of wide band gap (WBG) semiconductors, (e.g., SiC, GaN,..) materials and devices processing for power electronics devices. He is co-author of more than 250 papers in international journals and conference proceedings, several review articles, 5 book chapters, 3 patents, and he has given several invited talks and lectures on SiC and GaN at international conferences. He has been chairman of three international conferences, and he is member of the Steering Committee of the conferences ECSCRM and EXMATEC.